

Debajyoti Das

List of Publications by Year in descending order

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169
papers

3,475
citations

109137

35
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189595

50
g-index

169
all docs

169
docs citations

169
times ranked

2091
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoluminescence phenomena prevailing in c-axis oriented intrinsic ZnO thin films prepared by RF magnetron sputtering. RSC Advances, 2014, 4, 35735-35743.	1.7	176
2	Generally Applicable Self-Masked Dry Etching Technique for Nanotip Array Fabrication. Nano Letters, 2004, 4, 471-475.	4.5	147
3	Photocatalytic degradation of Rhodamine-B dye by stable ZnO nanostructures with different calcination temperature induced defects. Applied Surface Science, 2019, 465, 546-556.	3.1	127
4	A novel preparation technique for preparing hydrogenated amorphous silicon with a more rigid and stable Si network. Applied Physics Letters, 1991, 59, 1096-1098.	1.5	108
5	Properties of electron-beam-evaporated tin oxide films. Thin Solid Films, 1987, 147, 321-331.	0.8	96
6	Self-doped TiO ₂ nanowires in TiO ₂ -B single phase, TiO ₂ -B/anatase and TiO ₂ -anatase/rutile heterojunctions demonstrating individual superiority in photocatalytic activity under visible and UV light. Applied Surface Science, 2018, 455, 1106-1115.	3.1	67
7	Properties of tin oxide films prepared by reactive electron beam evaporation. Thin Solid Films, 1987, 149, 291-301.	0.8	65
8	Nanocrystalline silicon films prepared from silane plasma in RF-PECVD, using helium dilution without hydrogen: structural and optical characterization. Nanotechnology, 2007, 18, 415704.	1.3	65
9	Narrow Band-Gap a-Si:H with Improved Minority Carrier-Transport Prepared by Chemical Annealing. Japanese Journal of Applied Physics, 1991, 30, L239-L242.	0.8	64
10	Characterization of the Si:H network during transformation from amorphous to micro- and nanocrystalline structures. Journal of Applied Physics, 2006, 100, 103701.	1.1	54
11	Low temperature grown ZnO:Ga films with predominant c-axis orientation in wurtzite structure demonstrating high conductance, transmittance and photoluminescence. RSC Advances, 2016, 6, 6144-6153.	1.7	53
12	Characterization of tin doped indium oxide films prepared by electron beam evaporation. Solar Energy Materials and Solar Cells, 1986, 13, 11-23.	0.4	51
13	Conducting wide band gap nc-Si/a-SiC:H films for window layers in nc-Si solar cells. Journal of Materials Chemistry A, 2013, 1, 14744.	5.2	50
14	Electrical transport phenomena prevailing in undoped nc-Si/a-SiNx:H thin films prepared by inductively coupled plasma chemical vapor deposition. Journal of Applied Physics, 2013, 114, .	1.1	50
15	Control of hydrogenation and modulation of the structural network in Si:H by interrupted growth and H-plasma treatment. Physical Review B, 1995, 51, 10729-10736.	1.1	49
16	Wide optical-gap a-SiO:H films prepared by rf glow discharge. Journal of Non-Crystalline Solids, 1997, 210, 148-154.	1.5	47
17	Transparent and conducting intrinsic ZnO thin films prepared at high growth-rate with c-axis orientation and pyramidal surface texture. Applied Surface Science, 2013, 286, 397-404.	3.1	46
18	ZnO-Cu O heterostructure photocatalyst for efficient dye degradation. Journal of Physics and Chemistry of Solids, 2020, 143, 109463.	1.9	46

#	ARTICLE	IF	CITATIONS
19	Infrared vibrational spectra of hydrogenated amorphous silicon carbide thin films prepared by glow discharge. <i>Solar Energy Materials and Solar Cells</i> , 1987, 15, 45-57.	0.4	45
20	Controlling the growth of nanocrystalline silicon by tuning negative substrate bias. <i>Solar Energy Materials and Solar Cells</i> , 2011, 95, 3181-3188.	3.0	45
21	Tunable photoluminescence from nc-Si/a-SiN _x :H quantum dot thin films prepared by ICP-CVD. <i>Physical Chemistry Chemical Physics</i> , 2013, 15, 3881.	1.3	45
22	Optimization of Si doping in ZnO thin films and fabrication of n-ZnO:Si/p-Si heterojunction solar cells. <i>Journal of Alloys and Compounds</i> , 2020, 824, 153902.	2.8	45
23	Heterogeneity in microcrystalline-transition state: Origin of Si-nucleation and microcrystallization at higher rf power from Ar-diluted SiH ₄ plasma. <i>Journal of Applied Physics</i> , 2001, 89, 3041-3048.	1.1	44
24	Characterization of undoped ¹³ C-SiO:H films prepared from (SiH ₄ +CO ₂ +H ₂)-plasma in RF glow discharge. <i>Solar Energy Materials and Solar Cells</i> , 2000, 63, 285-297.	3.0	43
25	Studies on the structural properties of SiO:H films prepared from (SiH ₄ +CO ₂ +He) plasma in RF-PECVD. <i>Solar Energy Materials and Solar Cells</i> , 2009, 93, 588-596.	3.0	42
26	Nanocrystalline silicon thin films prepared by low pressure planar inductively coupled plasma. <i>Applied Surface Science</i> , 2013, 276, 249-257.	3.1	42
27	Role of hydrogen in controlling the growth of ¹³ C-Si:H films from argon diluted SiH ₄ plasma. <i>Journal of Applied Physics</i> , 2002, 91, 5442-5448.	1.1	41
28	Structural studies on Si:H network by Raman, micro-photoluminescence, electron microscopy and ultraviolet ellipsometry: effect of Ar dilution to the SiH ₄ -plasma. <i>Thin Solid Films</i> , 2005, 476, 237-245.	0.8	41
29	ZnO/CdS/CuS heterostructure: A suitable candidate for applications in visible-light photocatalysis. <i>Journal of Physics and Chemistry of Solids</i> , 2022, 160, 110344.	1.9	41
30	Micro-Raman and ultraviolet ellipsometry studies on ¹³ C-Si:H films prepared by H ₂ dilution to the Ar-assisted SiH ₄ plasma in radio frequency glow discharge. <i>Journal of Applied Physics</i> , 2003, 93, 2528-2535.	1.1	39
31	A novel approach towards silicon nanotechnology. <i>Journal Physics D: Applied Physics</i> , 2003, 36, 2335-2346.	1.3	39
32	Quantum confinement effects in nano-silicon thin films. <i>Solid State Communications</i> , 1998, 108, 983-987.	0.9	38
33	Anti-reflection coatings for silicon solar cells from hydrogenated diamond like carbon. <i>Applied Surface Science</i> , 2015, 345, 204-215.	3.1	38
34	Superior photocatalytic dye degradation under visible light by reduced graphene oxide laminated TiO ₂ -B nanowire composite. <i>Journal of Environmental Chemical Engineering</i> , 2019, 7, 103358.	3.3	37
35	Effect of deposition temperature on the growth of nanocrystalline silicon network from helium diluted silane plasma. <i>Journal Physics D: Applied Physics</i> , 2008, 41, 155420.	1.3	36
36	Correlation between the physical parameters of the ¹³ C-nc-Si absorber layer grown by 27.12 MHz plasma with the nc-Si solar cell parameters. <i>Applied Surface Science</i> , 2017, 416, 980-987.	3.1	36

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37	Properties of a-SiO:H films prepared by RF glow discharge. <i>Solar Energy Materials and Solar Cells</i> , 2000, 60, 167-179.	3.0	35
38	Hydrogen induced promotion of nanocrystallization from He-diluted SiH ₄ plasma. <i>Journal Physics D: Applied Physics</i> , 2008, 41, 085303.	1.3	35
39	Photoluminescent silicon quantum dots in core/shell configuration: synthesis by low temperature and spontaneous plasma processing. <i>Nanotechnology</i> , 2011, 22, 055601.	1.3	35
40	Further improvements in conducting and transparent properties of ZnO:Ga films with perpetual c-axis orientation: Materials optimization and application in silicon solar cells. <i>Applied Surface Science</i> , 2017, 411, 315-320.	3.1	35
41	Reduced Graphene Oxide-Laminated One-Dimensional TiO ₂ "Bronze Nanowire Composite: An Efficient Photoanode Material for Dye-Sensitized Solar Cells. <i>ACS Omega</i> , 2021, 6, 4362-4373.	1.6	34
42	Enhancement of multiferroic properties and unusual magnetic phase transition in Eu doped bismuth ferrite nanoparticles. <i>New Journal of Chemistry</i> , 2017, 41, 10985-10991.	1.4	33
43	Synthesis of diameter controlled multiwall carbon nanotubes by microwave plasma-CVD on low-temperature and chemically processed Fe nanoparticle catalysts. <i>Applied Surface Science</i> , 2020, 515, 146043.	3.1	31
44	Narrow band gap reduced TiO ₂ -B:Cu nanowire heterostructures for efficient visible light absorption, charge separation and photocatalytic degradation. <i>Applied Surface Science</i> , 2020, 506, 144880.	3.1	29
45	Development of nc-Si/Al-SiN/SiO ₂ /H Thin Films for Photovoltaic and Light-Emitting Applications. <i>Science of Advanced Materials</i> , 2013, 5, 188-198.	0.1	28
46	Helium versus hydrogen dilution in the optimization of polymorphous silicon solar cells. <i>Journal of Non-Crystalline Solids</i> , 2004, 338-340, 668-672.	1.5	26
47	Realizing a variety of carbon nanostructures at low temperature using MW-PECVD of (CH ₄ +H ₂) plasma. <i>Applied Surface Science</i> , 2013, 273, 806-815.	3.1	26
48	Nanocrystalline silicon thin films from SiH ₄ plasma diluted by H ₂ and He in RF-PECVD. <i>Journal of Physics and Chemistry of Solids</i> , 2017, 105, 90-98.	1.9	26
49	Control of Crystallization at Low Thickness in Åµc-Si:H Films Using Layer-by-Layer Growth Scheme. <i>Japanese Journal of Applied Physics</i> , 1999, 38, L1087-L1090.	0.8	24
50	Ternary ZnCdSO composite photocatalyst for efficient dye degradation under visible light retaining Z-scheme of migration pathways for the photogenerated charge carriers. <i>Solar Energy Materials and Solar Cells</i> , 2020, 217, 110674.	3.0	24
51	Effect of hydrogen in controlling the structural orientation of ZnO:Ga:H as transparent conducting oxide films suitable for applications in stacked layer devices. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 20450-20458.	1.3	22
52	Promotion of microcrystallization by argon in moderately hydrogen diluted silane plasma. <i>Solar Energy Materials and Solar Cells</i> , 2002, 74, 407-413.	3.0	21
53	Further improvements of nano-diamond structures on unheated substrates by optimization of parameters with secondary plasma in MW-PECVD. <i>Surface and Coatings Technology</i> , 2015, 272, 357-365.	2.2	21
54	SiO _x nanowires with intrinsic nC-Si quantum dots: the enhancement of the optical absorption and photoluminescence. <i>Journal of Materials Chemistry C</i> , 2013, 1, 6623.	2.7	20

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55	Low temperature growth of carbon nanotubes by microwave plasma stimulated by CO ₂ as weak oxidant and guided by shadow masking. <i>Diamond and Related Materials</i> , 2018, 88, 204-214.	1.8	20
56	Further optimization of ITO films at the melting point of Sn and configuration of Ohmic contact at the c-Si/ITO interface. <i>Applied Surface Science</i> , 2019, 481, 16-24.	3.1	20
57	Improved TCO characteristics of ZnO:Si films via utilization of Si ⁴⁺ ionized donor states and its application in n-SZO/p-Si heterojunction solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2020, 206, 110278.	3.0	20
58	Autogenic single p/n-junction solar cells from black-Si nano-grass structures of p-to-n type self-converted electronic configuration. <i>Nanoscale</i> , 2020, 12, 15371-15382.	2.8	20
59	Graphitic carbon nitride (g-C ₃ N ₄) incorporated TiO ₂ @B nanowires as efficient photoanode material in dye sensitized solar cells. <i>Materials Chemistry and Physics</i> , 2021, 266, 124520.	2.0	19
60	Morphological variations of ZnO nanostructures and its influence on the photovoltaic performance when used as photoanodes in dye sensitized solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2022, 243, 111811.	3.0	19
61	Quantum size effects on the optical properties of nc-Si QDs embedded in an a-SiO _x matrix synthesized by spontaneous plasma processing. <i>Physical Chemistry Chemical Physics</i> , 2015, 17, 5063-5071.	1.3	18
62	Synthesis of CdS/GO modified ZnO heterostructure for visible light dye degradation applications. <i>Applied Surface Science</i> , 2021, 570, 151260.	3.1	18
63	Correlation of Electrical, Thermal and Structural Properties of Microcrystalline Silicon Thin Films. <i>Japanese Journal of Applied Physics</i> , 2002, 41, L229-L232.	0.8	17
64	Size effect on electronic transport in nc-Si/SiO core/shell quantum dots. <i>Materials Research Bulletin</i> , 2012, 47, 3625-3629.	2.7	17
65	Melting point of Sn as the optimal growth temperature in realizing the favored transparent conducting properties of In ₂ O ₃ :Sn films. <i>Journal of Alloys and Compounds</i> , 2018, 767, 642-650.	2.8	17
66	CdS Q-Dot-Impregnated TiO ₂ -B Nanowire-Based Photoanodes for Efficient Photovoltaic Conversion in Q-Dot Co-sensitized DSSC TM . <i>Energy & Fuels</i> , 2021, 35, 8246-8262.	2.5	17
67	Synthesis of nanocrystalline diamond embedded diamond-like carbon films on untreated glass substrates at low temperature using (C ₂ H ₂ +H ₂) gas composition in microwave plasma CVD. <i>Applied Surface Science</i> , 2022, 579, 152132.	3.1	17
68	Two-Step Visible Light Photocatalytic Dye Degradation Phenomena in Ag ₂ O-Impregnated ZnO Nanorods via Growth of Metallic Ag and Formation of ZnO/Ag ⁰ /Ag ₂ O Heterojunction Structures. <i>Langmuir</i> , 2022, 38, 4503-4520.	1.6	17
69	Microstructural association of diverse chemical constituents in nc-SiO _x :H network synthesized by spontaneous low temperature plasma processing. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2018, 103, 99-109.	1.3	16
70	Wide optical gap B-doped nc-Si thin films with advanced crystallinity and conductivity on transparent flexible substrates for potential low-cost flexible electronics including nc-Si superstrate p ⁺ -i ⁿ solar cells. <i>Materials Advances</i> , 2021, 2, 2055-2067.	2.6	16
71	Optical, electrical and structural properties of SiO _x :H films prepared from He dilution to the SiH ₄ plasma. <i>Journal Physics D: Applied Physics</i> , 2009, 42, 215404.	1.3	15
72	Low temperature synthesis of spherical nano-diamond. <i>Journal of Experimental Nanoscience</i> , 2014, 9, 818-824.	1.3	15

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73	Spectroscopic and microscopic studies of self-assembled nc-Si/a-SiC thin films grown by low pressure high density spontaneous plasma processing. <i>Physical Chemistry Chemical Physics</i> , 2014, 16, 25421-25431.	1.3	15
74	Effect of oxygen on the optical, electrical and structural properties of mixed-phase boron doped nanocrystalline silicon oxide thin films. <i>Applied Surface Science</i> , 2017, 423, 1161-1168.	3.1	15
75	Rigid amorphous silicon network from hydrogenated and fluorinated precursors in ECR-CVD. <i>Solar Energy Materials and Solar Cells</i> , 2004, 81, 155-168.	3.0	14
76	Effect of RF power on the formation and size evolution of nC-Si quantum dots in an amorphous SiOx matrix. <i>Journal of Materials Chemistry</i> , 2011, 21, 7452.	6.7	14
77	Low temperature plasma processing of nc-Si/a-SiN _x :H QD thin films with high carrier mobility and preferred (220) crystal orientation: a promising material for third generation solar cells. <i>RSC Advances</i> , 2014, 4, 36929-36939.	1.7	14
78	Preferential $\sim 220^\circ$ crystalline growth in nanocrystalline silicon films from 27.12 MHz SiH ₄ plasma for applications in solar cells. <i>RSC Advances</i> , 2015, 5, 54011-54018.	1.7	14
79	Controlling the opto-electronic properties of nc-SiOx:H films by promotion of $\sim 220^\circ$ orientation in the growth of ultra-nanocrystallites at the grain boundary. <i>Applied Surface Science</i> , 2018, 428, 757-766.	3.1	14
80	Narrow band gap high conducting nc-Si _{1-x} Ge _x :H absorber layers for tandem structure nc-Si solar cells. <i>Journal of Alloys and Compounds</i> , 2019, 806, 1529-1535.	2.8	14
81	Electrically active boron doping in the core of Si nanocrystals by planar inductively coupled plasma CVD. <i>Journal of Applied Physics</i> , 2019, 126, 155305.	1.1	14
82	Advanced nanocrystallinity with widened optical gap realized via microstructural control in P-doped silicon oxide thin films used as window layer in nc-Si solar cells. <i>Materials Chemistry and Physics</i> , 2020, 243, 122628.	2.0	14
83	Self-assembled nc-Si-QD/a-SiC thin films from planar ICP-CVD plasma without H ₂ -dilution: a combination of wide optical gap, high conductivity and preferred $\sim 220^\circ$ crystallographic orientation, uniquely appropriate for nc-Si solar cells. <i>RSC Advances</i> , 2016, 6, 3860-3869.	1.7	13
84	The growth of ZnO:Ga:Cu as new TCO film of advanced electrical, optical and structural quality. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2017, 91, 1-7.	1.3	13
85	Improvement in the optoelectronic properties of a-SiO:H films. <i>Journal of Materials Science</i> , 1999, 34, 1051-1054.	1.7	12
86	Effect of substrate bias on the promotion of nanocrystalline silicon growth from He-diluted SiH ₄ plasma at low temperature. <i>Journal of Materials Research</i> , 2012, 27, 1303-1313.	1.2	12
87	Spectroscopic studies on nanocrystalline silicon thin films prepared from H ₂ -diluted SiH ₄ -plasma in inductively coupled low pressure RF PECVD. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2014, 61, 95-100.	1.3	12
88	Superior optical response of size-controlled silicon nano-crystals in a-Si:H/nc-Si:H superlattice films for multi-junction solar cells. <i>RSC Advances</i> , 2015, 5, 61118-61126.	1.7	12
89	Development of optimum p-nc-Si window layers for nc-Si solar cells. <i>Physical Chemistry Chemical Physics</i> , 2017, 19, 21357-21363.	1.3	12
90	Characterization of a-SiGe: H films prepared by rf glow discharge. <i>Journal of Non-Crystalline Solids</i> , 1991, 128, 172-182.	1.5	11

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91	Wide Band Gap Si:H at Low H-Content Prepared by Interrupted Grown and H-Plasma Treatment. Japanese Journal of Applied Physics, 1994, 33, L571-L574.	0.8	11
92	Structural investigation of nC-Si/SiO _x :H thin films from He diluted (SiH ₄ +CO ₂) plasma at low temperature. Applied Surface Science, 2012, 259, 477-485.	3.1	11
93	Enhanced multiferroic, magnetodielectric and electrical properties of Sm doped Lanthanum ferrite nanoparticles. Journal of Materials Science: Materials in Electronics, 2019, 30, 10694-10710.	1.1	11
94	Nanocrystallization in Si:H and quantum size effect on optical gap. Bulletin of Materials Science, 1997, 20, 9-22.	0.8	10
95	Better control over the onset of microcrystallinity in fast-growing silicon network. Journal of Materials Research, 2004, 19, 2597-2603.	1.2	10
96	Rapid synthesis of nc-Si/a-SiN _x :H QD thin films by plasma processing for their cost effective applications in photonic and photovoltaic devices. RSC Advances, 2015, 5, 63572-63579.	1.7	10
97	Structural studies of n-type nc-Si QD thin films for nc-Si solar cells. Journal of Physics and Chemistry of Solids, 2017, 111, 115-122.	1.9	10
98	Optimization in the nanostructural evolution of hydrogenated silicon germanium thin film in RF-PECVD. Physica E: Low-Dimensional Systems and Nanostructures, 2019, 111, 20-28.	1.3	10
99	Reverse Meyer-Neldel rule prevailing in the hole transport of B-doped nc-SiO _x :H thin films sustaining degeneracy and performing as suitable window of nc-Si solar cells. Physica E: Low-Dimensional Systems and Nanostructures, 2021, 128, 114615.	1.3	10
100	Complex Dielectric Characteristics, ac-Conductivity, and Impedance Spectroscopy of B-Doped nc-SiO _x :H Thin Films. ACS Applied Electronic Materials, 2021, 3, 1634-1647.	2.0	10
101	Evolution of microcrystalline growth pattern by ultraviolet spectroscopic ellipsometry on Si:H films prepared by Hot-Wire CVD. Solid State Communications, 2003, 128, 397-402.	0.9	9
102	Micro-photoluminescence and micro-Raman studies near the amorphous-to-microcrystalline transition in Si:H. Solid State Communications, 2003, 127, 453-456.	0.9	9
103	Development of highly conducting p-type $\hat{1}/4$ c-Si:H films from minor diborane doping in highly hydrogenated SiH ₄ plasma. Materials Letters, 2004, 58, 980-985.	1.3	9
104	Nanocrystalline silicon prepared at high growth rate using helium dilution. Bulletin of Materials Science, 2008, 31, 467-471.	0.8	9
105	Self-assembled ultra-nanocrystalline silicon films with preferred $\hat{2} 2 0$ crystallographic orientation for solar cell applications. Applied Surface Science, 2015, 330, 134-141.	3.1	9
106	Opto-electronic properties of P-doped nc-Si QD/a-SiC:H thin films as foundation layer for all-Si solar cells in superstrate configuration. Journal of Applied Physics, 2016, 120, 025102.	1.1	9
107	Highly Conducting Undoped $\hat{\mu}$ c-SiO:H Films Prepared by RF Glow Discharge. Japanese Journal of Applied Physics, 1999, 38, L697-L699.	0.8	8
108	Changes in Optical and Electrical Phenomena Correlated to Structural Configuration in Nanocrystalline Silicon Network. Journal of the Electrochemical Society, 2011, 158, H1138.	1.3	8

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109	Self-assembled nc-Si/a-SiNx: H quantum dots thin films: An alternative solid-state light emitting material. <i>Journal of Luminescence</i> , 2015, 158, 11-18.	1.5	8
110	Phosphorus-doped nanocrystalline silicon-oxycarbide thin films. <i>Journal of Alloys and Compounds</i> , 2021, 876, 160094.	2.8	8
111	Device quality a-SiGe:H films for multijunction solar cells. <i>Journal of Non-Crystalline Solids</i> , 1989, 114, 552-554.	1.5	7
112	Synthesis of single-walled, bamboo-shaped and Y-junction carbon nanotubes using microwave plasma CVD on low-temperature and chemically processed catalysts. <i>Journal of Physics and Chemistry of Solids</i> , 2021, 152, 109971.	1.9	7
113	Influence of manganese on multiferroic and electrical properties of lanthanum ferrite nanoparticles. <i>Materials Research Express</i> , 2019, 6, 085032.	0.8	6
114	Nanocrystalline Diamond. , 2019, , 123-181.		6
115	Prominent c-axis oriented Si-doped ZnO thin film prepared at low substrate temperature in RF magnetron sputtering and its UV sensing in p-Si/n-SZO heterojunction structures. <i>Journal of Physics and Chemistry of Solids</i> , 2021, 151, 109907.	1.9	6
116	Optoelectronic and structural properties of Ge-rich narrow band gap nc-SixGe1-x absorber layer for tandem structure nc-Si solar cells. <i>Journal of Physics and Chemistry of Solids</i> , 2021, 154, 110055.	1.9	6
117	Evolution of nc-Si Network and the Control of Its Growth by He/H ₂ Plasma Assistance in SiH ₄ at PECVD. <i>Journal of Nanoscience and Nanotechnology</i> , 2009, 9, 5614-5621.	0.9	5
118	Low temperature growth of carbon nanotubes with aligned multiwalls by microwave plasma-CVD. <i>AIP Conference Proceedings</i> , 2017, , .	0.3	5
119	Growth of Nanostructured Diamond Films on Glass Substrates by Low-Temperature Microwave Plasma-Enhanced Chemical Vapor Deposition for Applications in Nanotribology. <i>ACS Applied Nano Materials</i> , 2022, 5, 3558-3571.	2.4	5
120	P-doped ¹¹ B-Si:H films at a very low thickness and high deposition rate: Suitable for application in solar cells. <i>Journal of Materials Research</i> , 2003, 18, 2371-2378.	1.2	4
121	Fabrication of double barrier structures in single layer c-Si QDs/a-SiOx films for realization of energy selective contacts for hot carrier solar cells. <i>Journal of Applied Physics</i> , 2017, 121, 044305.	1.1	4
122	Metastable titanium dioxide B-phase nanowire prepared by hydrothermal method. <i>AIP Conference Proceedings</i> , 2017, , .	0.3	4
123	Silicon nanostructure arrays prepared by single step metal assisted chemical etching from single crystal wafer. <i>AIP Conference Proceedings</i> , 2018, , .	0.3	4
124	Nano-diamond and Diamond-like Carbon Thin Films for Anti-Reflecting Coating Application on Silicon Solar Cells. <i>Materials Today: Proceedings</i> , 2018, 5, 23316-23320.	0.9	4
125	Effect of HF wet-etching and H ₂ -plasma polishing on the low-temperature growth of carbon nanotubes on stainless-steel substrates. <i>Journal of Physics and Chemistry of Solids</i> , 2022, 160, 110307.	1.9	4
126	Fabrication of highly transparent diamond-like carbon anti-reflecting coating for Si solar cell application. , 2014, , .		3

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127	Investigation of the vertical electrical transport in a-Si:H/nc-Si:H superlattice thin films. Physical Chemistry Chemical Physics, 2015, 17, 17063-17068.	1.3	3
128	Growth of highly aligned vertical Si-Nanorods and random Si-Nanowires by ICP-Plasma chemical etching of c-Si wafers. AIP Conference Proceedings, 2017, , .	0.3	3
129	Highly conducting p-type nanocrystalline silicon thin films preparation without additional hydrogen dilution. AIP Conference Proceedings, 2018, , .	0.3	3
130	Growth of Multiwall Carbon Nanotubes at 300Â°C Using CO ₂ as a Weak Oxidant to (CH ₄ +H ₂) Microwave Plasma. Materials Today: Proceedings, 2019, 18, 1411-1415.	0.9	3
131	Optimization of Nano-structured Tin Doped Indium Oxide Films Grown at Substrate Temperature close to the Melting Point of Tin. Materials Today: Proceedings, 2019, 18, 1304-1309.	0.9	3
132	Single-step fabrication of single-junction c-Si nano-structured solar cells by optimization of plasma etching parameters. Journal of Alloys and Compounds, 2020, 847, 155352.	2.8	3
133	Optimal H ₂ -dilution playing key role in accomplishing significant nanocrystallinity with both Si and Ge moieties in SiGe nanocomposite thin film network. Applied Surface Science, 2022, 597, 153657.	3.1	3
134	Black silicon prepared by H ₂ plasma etching of single crystal wafers in PECVD. AIP Conference Proceedings, 2017, , .	0.3	2
135	Significant band gap narrowing of reduced monoclinic TiO ₂ -B porous nanowire decorated by ternary hybrid of Cu/Cu ₂ O-nanoparticle for efficient visible light absorption. Materials Today: Proceedings, 2019, 18, 1430-1434.	0.9	2
136	Low-temperature synthesis of conducting boron-doped nanocrystalline silicon oxide thin films as the window layer of solar cells. Current Applied Physics, 2021, 23, 42-51.	1.1	2
137	Frequency and temperature dependent electrical characteristics of P-doped nc-SiO _x :H thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 272, 115361.	1.7	2
138	Growth of diamond-like carbon films with significant nanocrystalline phases in a low-pressure high-density CH ₄ plasma in ICP-CVD: Effect of negative dc substrate bias. Applied Surface Science, 2022, 596, 153638.	3.1	2
139	Preferred C-axis oriented photoluminescent ZnO thin films prepared by RF magnetron sputtering. , 2013, , .		1
140	Structural characterization of silicon thin film superlattice grown at low temperature. Superlattices and Microstructures, 2017, 111, 385-395.	1.4	1
141	Maintaining significant ultra-nanocrystallinity in electrically conducting boron doped silicon thin layers for solar cells. AIP Conference Proceedings, 2018, , .	0.3	1
142	Vertically aligned silicon nanowire arrays prepared by silver assisted single step chemical etching. AIP Conference Proceedings, 2020, , .	0.3	1
143	Low temperature growth of a-Si/nc-Si superlattice thin films demonstrating enhanced optical absorption. AIP Conference Proceedings, 2020, , .	0.3	1
144	Synthesis of cost-effective g-C ₃ N ₄ /ZnO heterostructure photocatalyst for methyl orange (MO) dye degradation. AIP Conference Proceedings, 2020, , .	0.3	1

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